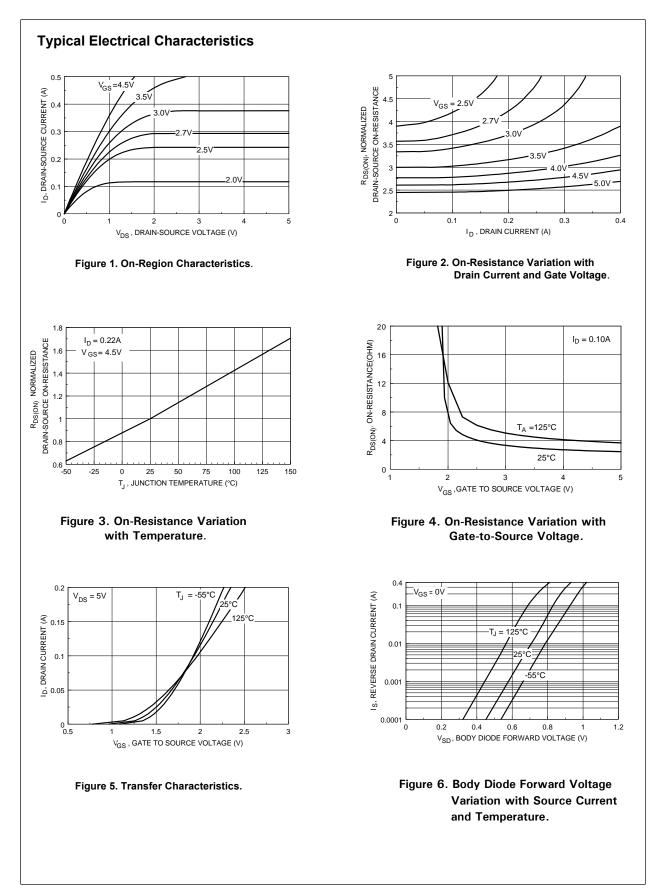
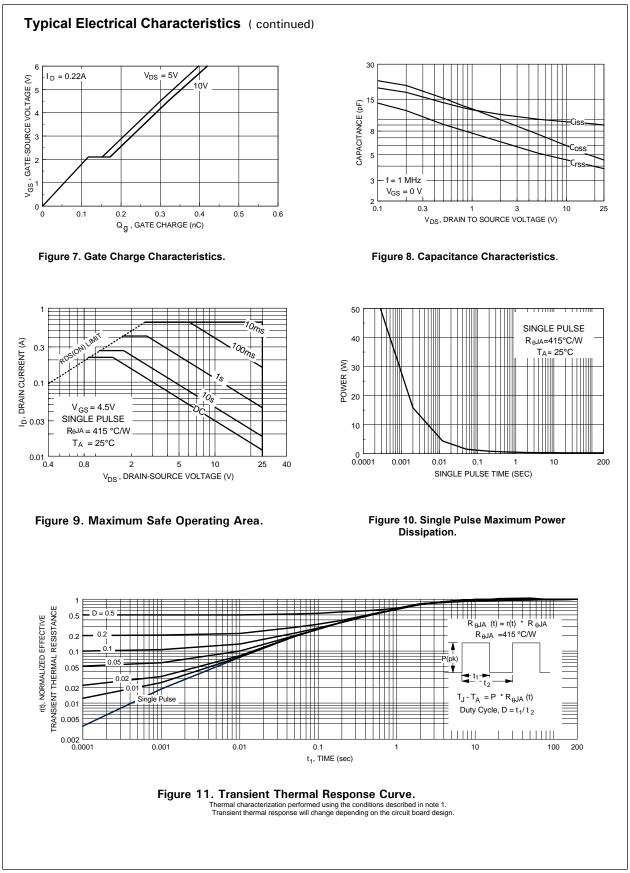
	IRCHILD				July 1999
-	6301N N-Channel, Digital	FET			
General Description These dual N-Channel logic level enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs.			 Features 25 V, 0.22 A continuous, 0.65 A peak. R_{DS(ON)} = 4 Ω @ V_{GS} = 4.5 V, R_{DS(ON)} = 5 Ω @ V_{GS} = 2.7 V. Very low level gate drive requirements allowing direct operation in 3 V circuits (V_{GS(th)} < 1.5 V). Gate-Source Zener for ESD ruggedness (>6kV Human Body Model). Compact industry standard SC70-6 surface mount package. 		
(÷	8.88 199			
SC7	0-6 SOT-23	SuperSOT [™] -6	SuperSOT [™] -8	SO-8	SOT-223
	D1 S2	D2 G1	L	or 4 *	6 or 3
Units in: Absol	G2 D1 SC70-6 SC70-6 SC70-6 SC70-6	G1 1 nterchangeable. ion and will not affect the fu	2 nctionality of the device.		5 or 2 4 or 1 *
Units ins Absol Symbol	G2 D1 OUTS are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter	G1 1 nterchangeable. ion and will not affect the fu	2 nctionality of the device.	TOT 5 3 or 6 3 or 6	5 or 2 4 or 1 *
	outs are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter Drain-Source Voltage	G1 1 nterchangeable. ion and will not affect the fu	2 nctionality of the device.	TDG6301N 25	5 or 2 4 or 1 *
Units in: Absol Symbol / _{DSS} / _{GSS}	outs are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter Drain-Source Voltage Gate-Source Voltage	$G1^{-1}$	2 nctionality of the device.	TOT 5 3 or 6 3 or 6	5 or 2 4 or 1 *
Units ins	G2 D1 G2 D1 G2 SC70-6 SC70-7	$G1^{-1}$	2 nctionality of the device.	EDG6301N 25 8 0.22	5 or 2 4 or 1 * Units V V
Units in: Absol Symbol /DSS /GSS D D	outs are symmetrical; pin 1 and 4 are i side the carrier can be of either orientat ute Maximum Ratings Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Current - Cor - Pute	$G1^{T}$ nterchangeable. ion and will not affect the fut $T_A = 25^{\circ}C \text{ unless otherw}$ ntinuous sed (Note 1)	ctionality of the device.	TOT 5 3 or 6 3 or 6 5 OF 6	5 or 2 4 or 1 * Units V V A
Units ins Absol Symbol Coss	G2 D1 SC70-6 SC70-7 SC70-7	G1 I I I I I I I I I I I I I I I I I I I	ctionality of the device.	EDG6301N 25 8 0.22 0.65 0.3	5 or 2 4 or 1 * V V V V W
Units in: Absol Symbol V _{DSS} V _{GSS} b C C C C C C C C C C C C C	G2 D1 G2 S D1 G2 S S SC70-6 S S S outs are symmetrical; pin 1 and 4 are i S S S outs are symmetrical; pin 1 and 4 are i S S S ute Maximum Ratings Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Current - Cor - Puls Maximum Power Dissipation Operating and Storage Temper Electrostatic Discharge Rating S	G1 I I I I I I I I I I I I I I I I I I I	ctionality of the device.	Tor 5 Bor 6 Bor 6 Bor 6 Bor 6 Cor 5 0.22 0.65 0.3 -55 to 150	5 or 2 4 or 1 * V V V A W °C

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS					•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	25			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		25		mV /°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20 V, V_{GS} = 0 V$			1	μA
		$T_{J} = 55^{\circ}C$			10	μA
I _{GSS}	Gate - Body Leakage Current	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
ON CHARA	CTERISTICS (Note 2)			1	1	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.65	0.85	1.5	V
$\Delta V_{GS(th)} / \Delta T_{J}$	Gate Threshold Voltage Temp.Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		-2.1		mV /°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_{D} = 0.22 \text{ A}$		2.6	4	Ω
		T _J =125°C		5.3	7	
		$V_{GS} = 2.7 \text{ V}, I_{D} = 0.19 \text{ A}$		3.7	5	
I _{D(ON)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	0.22			А
9 _{FS}	Forward Transconductance	$V_{DS} = 5 V, I_{D} = 0.22 A$		0.2		S
DYNAMIC C	HARACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		9.5		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		6		pF
C _{rss}	Reverse Transfer Capacitance			1.3		pF
SWITCHING	CHARACTERISTICS (Note 2)					
t _{D(on)}	Tum - On Delay Time	$V_{DD} = 5 V, I_{D} = 0.5 A,$		5	10	ns
Ļ	Turn - On Rise Time	$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 50 \Omega$		4.5	10	ns
t _{D(off)}	Turn - Off Delay Time			4	8	ns
t _r	Turn - Off Fall Time			3.2	7	ns
Q _g	Total Gate Charge	$V_{DS} = 5 V, I_D = 0.22 A,$		0.29	0.4	nC
Q _{gs}	Gate-Source Charge	$V_{GS}^{00} = 4.5 V$		0.12		nC
Q _{gd}	Gate-Drain Charge	Charge		0.03		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAXIM	UM RATINGS				
l _s	Maximum Continuous Source Current				0.25	A
V _{SD}	Drain-Source Diode Forward Voltage	$V_{\rm GS} = 0 \ V, \ I_{\rm S} = 0.25 \ A \ ({\rm Note} \ 2)$		0.8	1.2	V

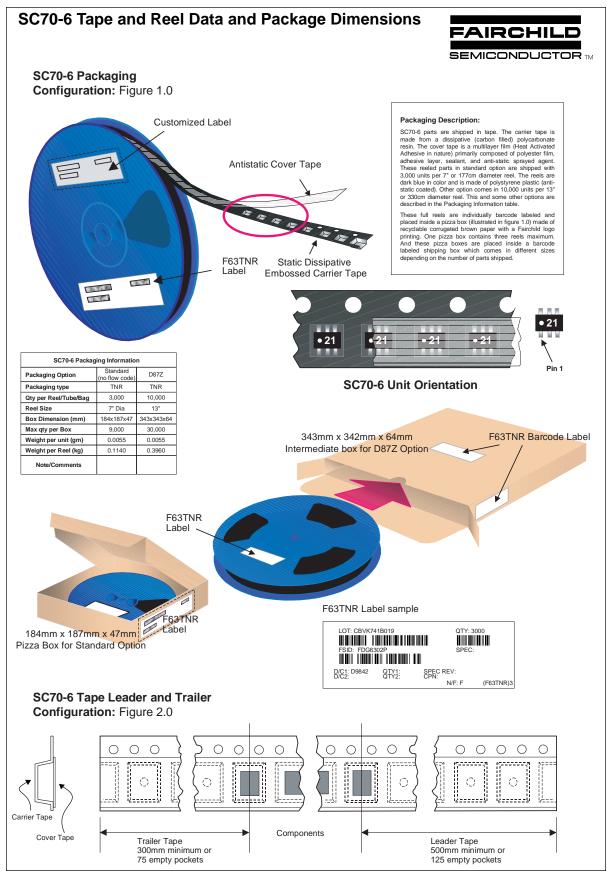
Notes:

1. R_{pk} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{pk} is guaranteed y design while $R_{y_{0}A}$ is determined by the user's board design. $R_{y_{0}A} = 415^{\circ}$ C/W on minimum pad mounting on FR-4 board in still air. 2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

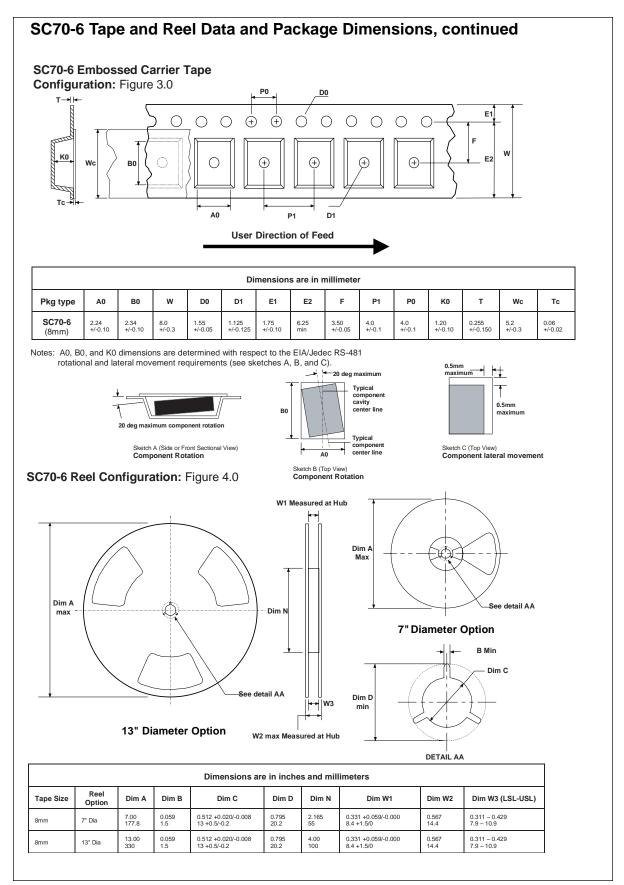


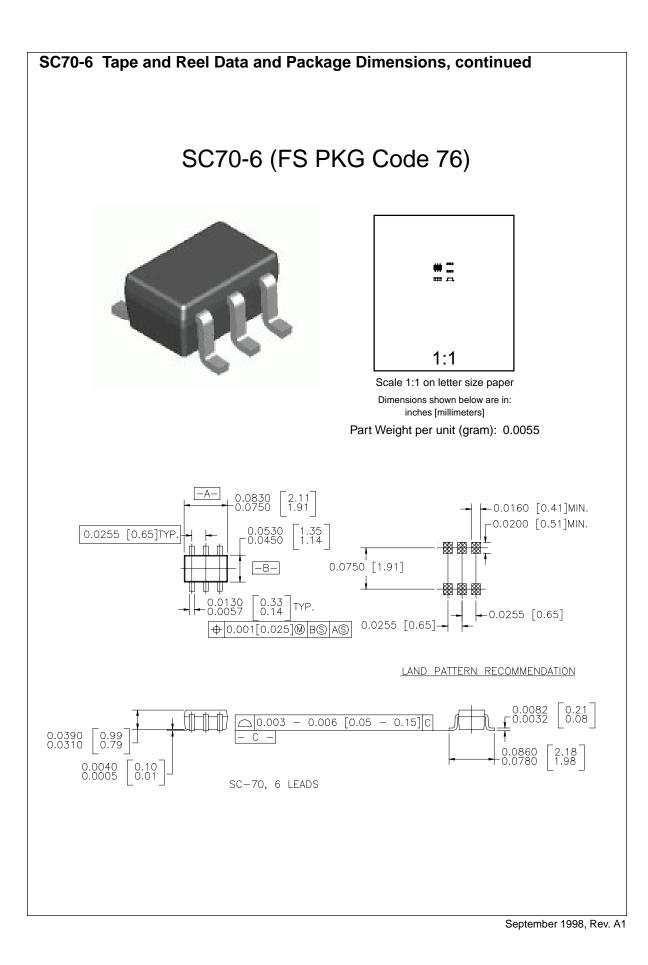


FDG6301N Rev.E1



August 1999, Rev. C





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